

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((conduct\$3 metal) near50 oxide near50 (substrate wafer) near50 hydrogen near50 (heat\$3 anneal\$3) near50 (separat\$3 delineat\$3 detach\$3 peel\$3)).clm.	US-PGPU B	OR	ON	2006/05/29 10:29
L2	162	((conduct\$3 metal) and oxide and (substrate wafer) and hydrogen and (heat\$3 anneal\$3) and (separat\$3 delineat\$3 detach\$3 peel\$3)).clm.	US-PGPU B	OR	ON	2006/05/29 10:30
L3	3	((conduct\$3 metal) same oxide same (substrate wafer) same hydrogen same (heat\$3 anneal\$3) same (separat\$3 delineat\$3 detach\$3 peel\$3)).clm.	US-PGPU B	OR	ON	2006/05/29 10:30

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8	(metal near50 oxide near50 (substrate wafer) near50 hydrogen near50 (heat\$3 anneal\$3) near50 (separat\$3 peel\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2006/05/29 09:55
L2	8	((conduct\$3 metal) near50 oxide near50 (substrate wafer) near50 hydrogen near50 (heat\$3 anneal\$3) near50 (separat\$3 peel\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2006/05/29 09:57
L3	8	((conduct\$3 metal) near50 oxide near50 (substrate wafer) near50 hydrogen near50 (heat\$3 anneal\$3) near50 (separat\$3 delineat\$3 detach\$3 peel\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2006/05/29 09:58
L4	74	((conduct\$3 metal) and oxide and (substrate wafer) and hydrogen and (heat\$3 anneal\$3) and (separat\$3 delineat\$3 detach\$3 peel\$3))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/05/29 09:58